

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	4	kV
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($T_j=25$ unless otherwise specified)

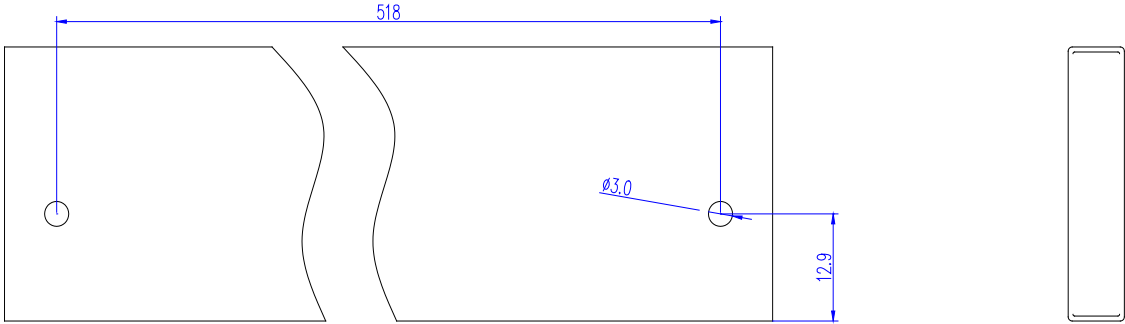
Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	20	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=150$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	40	mA
				55	
I_H	$I_T=500mA$		MAX.	30	mA
dV/dt	$V_D=540V$ Gate Open $T_j=150$		MIN.	1000	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s, T_j=150$		MIN.	12	A/ms

t_{on} $I_G=40mA I_A=200mA I_R=20mA$
 $T_j=25$

FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



T1620H-8E



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